

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		-20	V
V_{GSS}	Gate-Source Voltage		± 12	
I_{D}^*	Continuous Drain Current	$T_A = 25^\circ\text{C}$	-3.5	A
		$T_A = 70^\circ\text{C}$	-2.8	
I_{DM}^*	Pulsed Drain Current	$T_A = 25^\circ\text{C}$	-14	
		$T_A = 70^\circ\text{C}$	-11.2	
I_{S}^*	Diode Continuous Forward Current		-1	$^\circ\text{C}$
T_{J}	Maximum Junction Temperature		150	
T_{STG}	Storage Temperature Range		-55 to 150	
P_{D}^*	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	1.4	W
		$T_A = 70^\circ\text{C}$	0.9	
$R_{\theta\text{JA}}^*$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	90	$^\circ\text{C/W}$
		Steady state	125	

Note * : Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

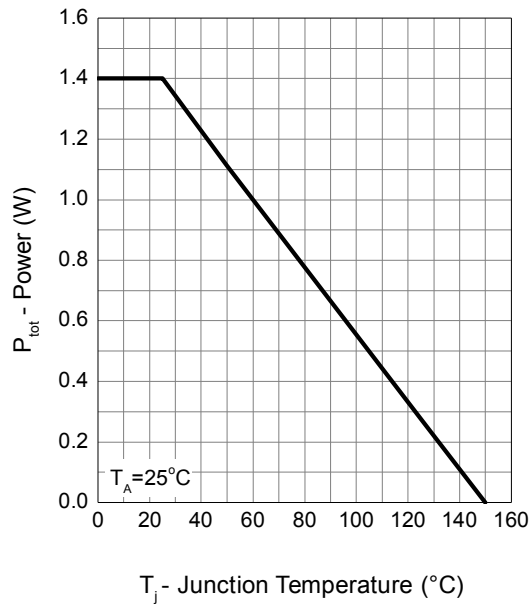
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V, V _{GS} =0V T _J =85°C	-	-	-1 -30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-0.5	-0.7	-1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±10V, V _{DS} =0V	-	-	±10	μA
R _{DS(ON)} ^a	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _{DS} =-3.3A	-	60	75	mΩ
		V _{GS} =-2.5V, I _{DS} =-2.1A	-	85	115	
		V _{GS} =-1.8V, I _{DS} =-0.9A	-	125	188	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.7	-1	V
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	10.7	-	Ω
C _{iSS}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, Frequency=1.0MHz	-	365	-	pF
C _{oSS}	Output Capacitance		-	75	-	
C _{rSS}	Reverse Transfer Capacitance		-	60	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-10V, R _L =10Ω, I _{DS} =-1A, V _{GEN} =-4.5V, R _G =6Ω	-	6.8	-	ns
t _r	Turn-on Rise Time		-	13.8	-	
t _{d(OFF)}	Turn-off Delay Time		-	30	-	
t _f	Turn-off Fall Time		-	23	-	
t _{rr}	Reverse Recovery Time	I _{SD} =-3.3A, dI _{SD} /dt =100A/μs	-	16	-	nC
Q _{rr}	Reverse Recovery Charge		-	6	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _{DS} =-3.3A	-	4.6	-	nC
Q _{gs}	Gate-Source Charge		-	0.7	-	
Q _{gd}	Gate-Drain Charge		-	1.8	-	

Note a : Pulse test; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

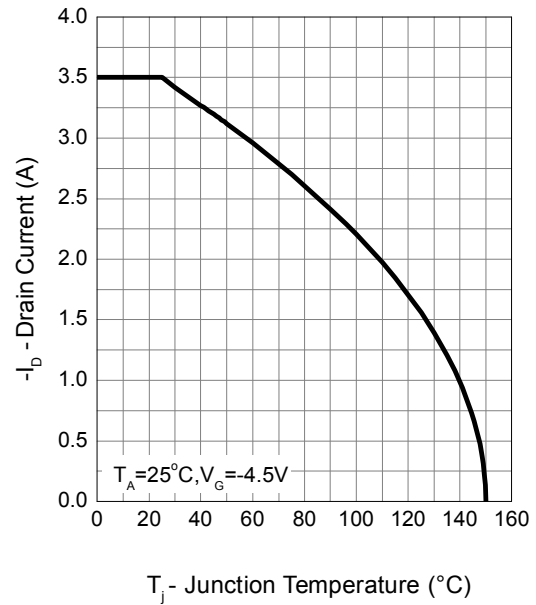
Note b : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

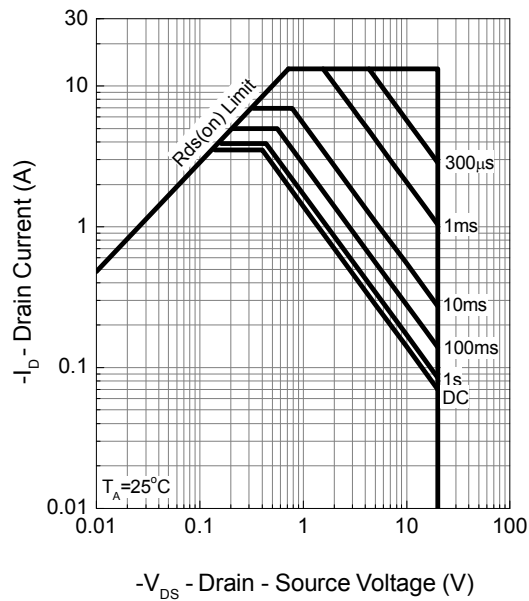
Power Dissipation



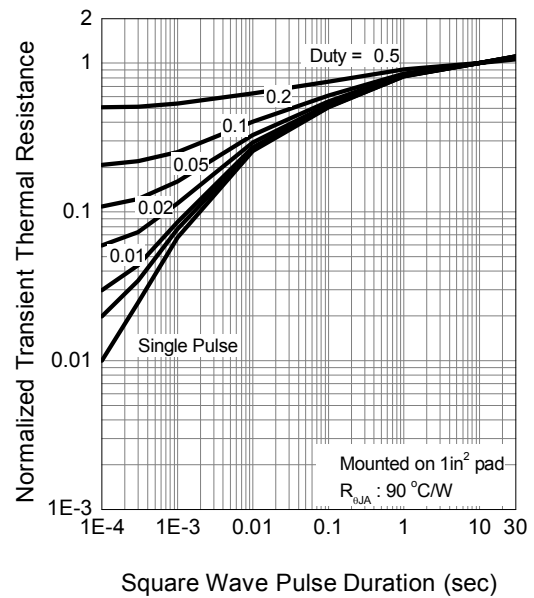
Drain Current



Safe Operation Area

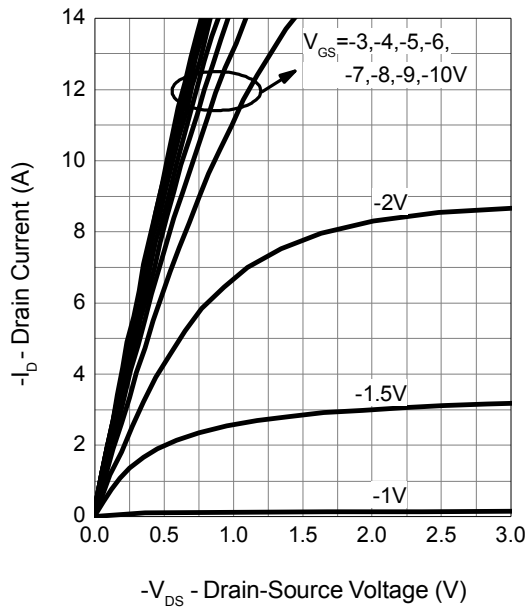


Thermal Transient Impedance

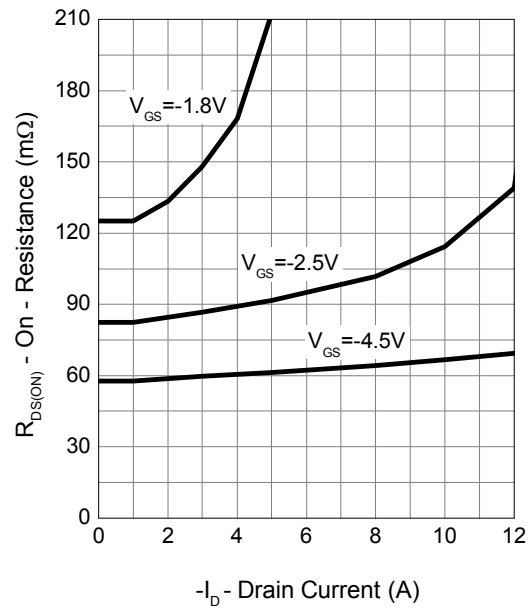


Typical Operating Characteristics (Cont.)

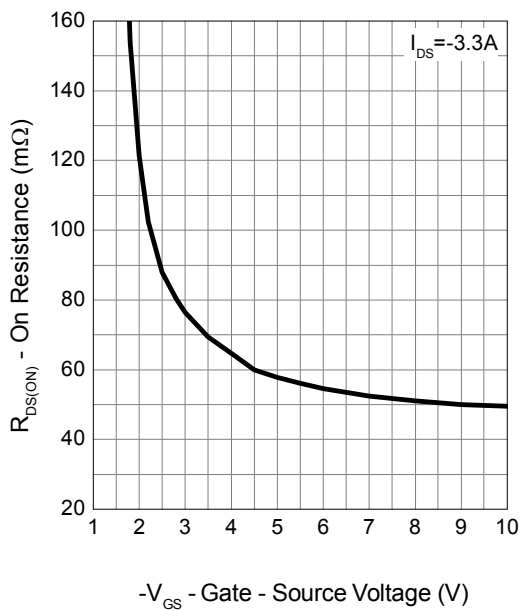
Output Characteristics



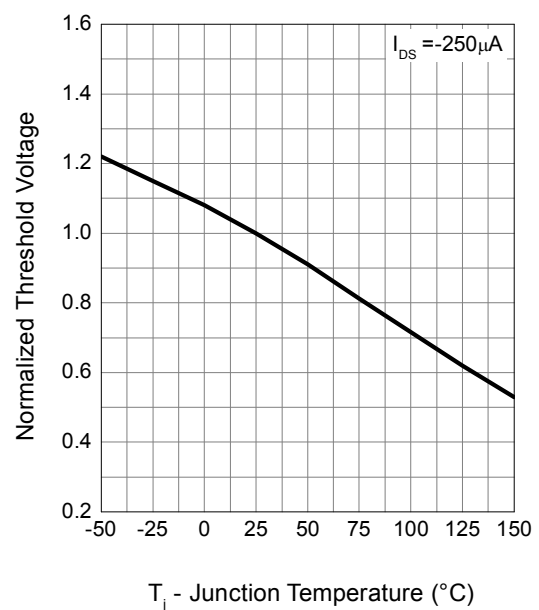
Drain-Source On Resistance



Gate-Source On Resistance

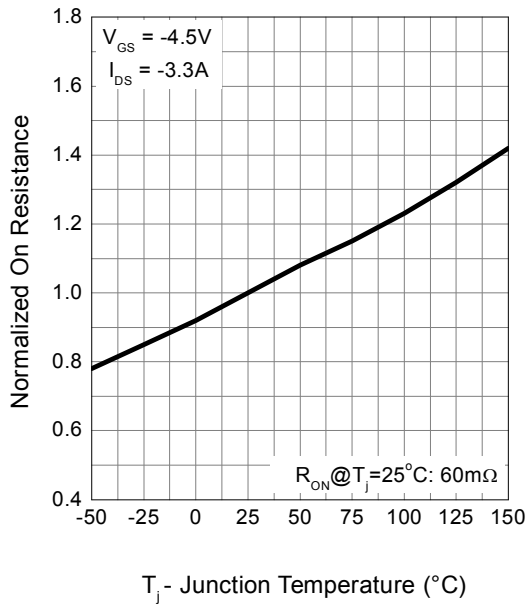


Gate Threshold Voltage

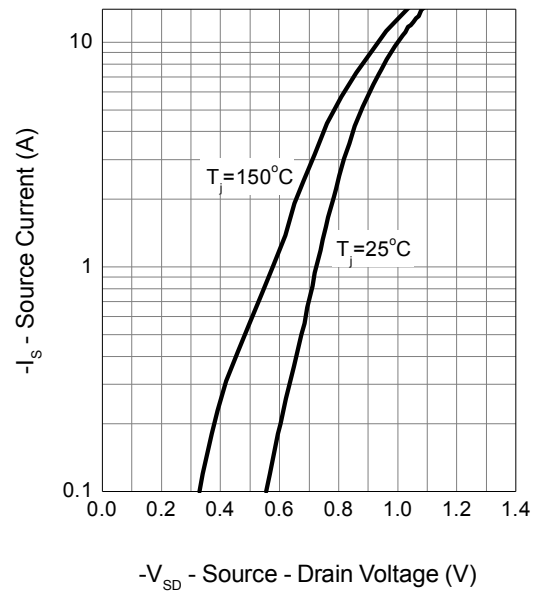


Typical Operating Characteristics (Cont.)

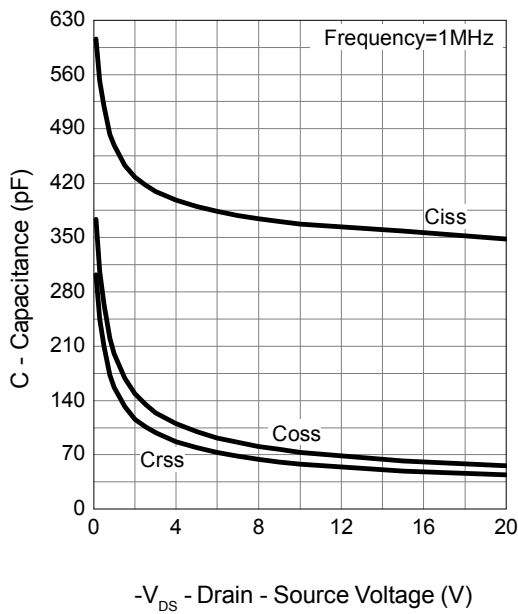
Drain-Source On Resistance



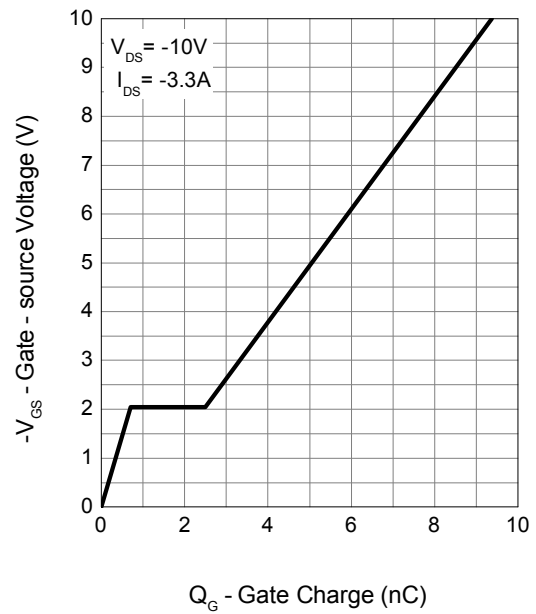
Source-Drain Diode Forward



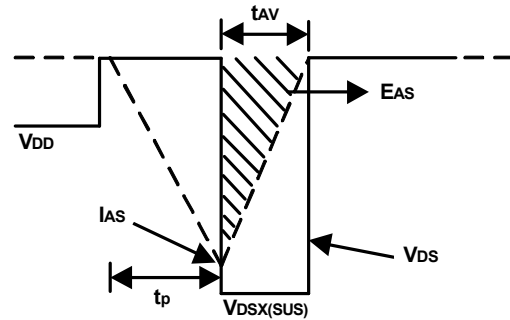
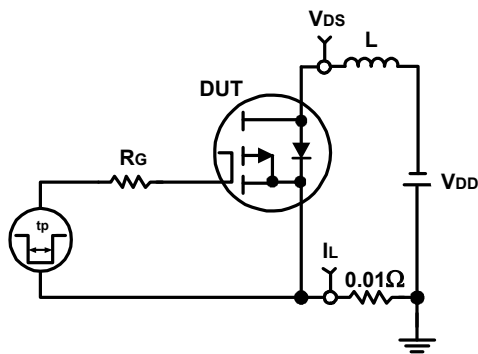
Capacitance



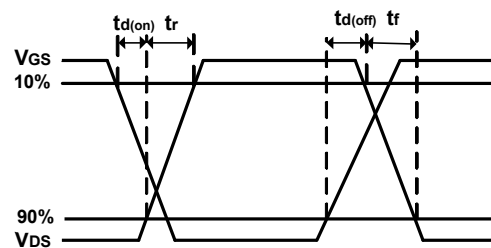
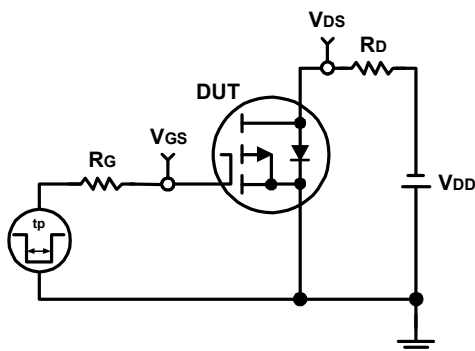
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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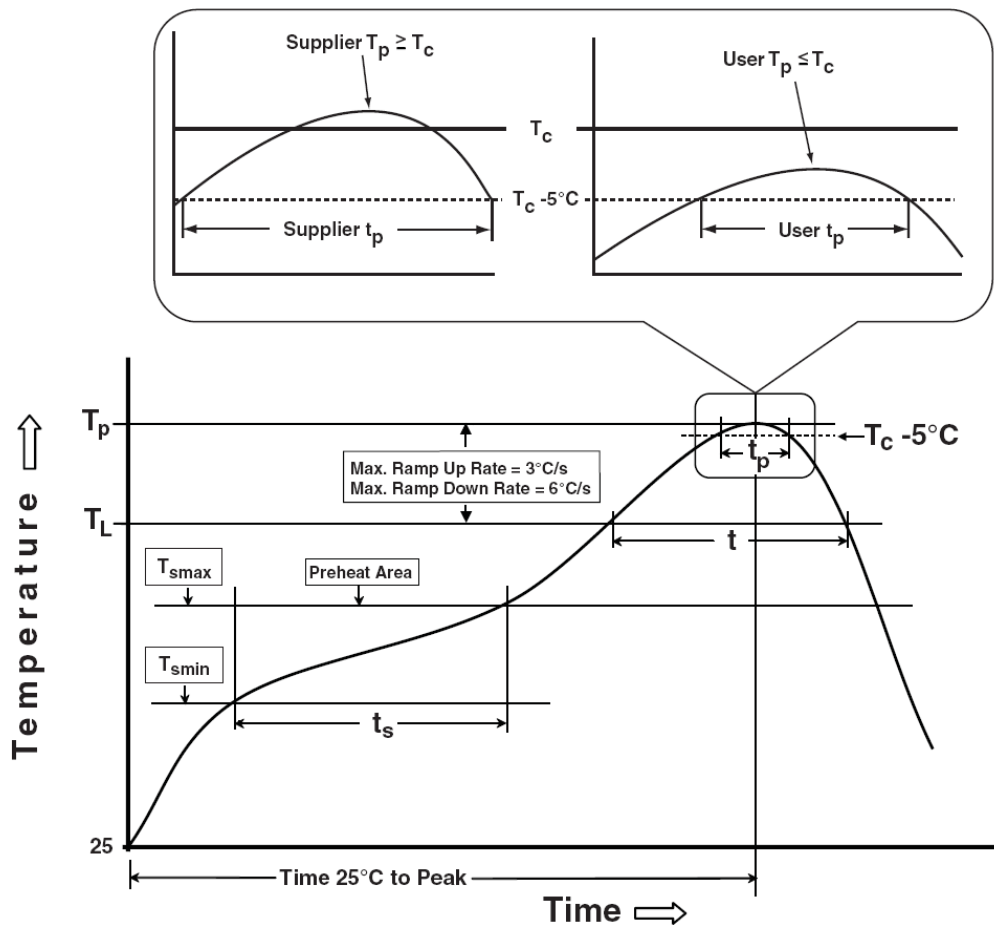
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

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